

Page 1 of 24

DIODES, MICROWAVE, SILICON, PIN, ULTRA FAST SWITCHING

BASED ON TYPES DH50052 TO DH50057 AND EH50052 TO EH50057

ESCC Detail Specification No. 5513/036

Issue 6	January 2018



Document Custodian: European Space Agency - see https://escies.org



No. 5513/036

ISSUE 6

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2018. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



No. 5513/036

ISSUE 6

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

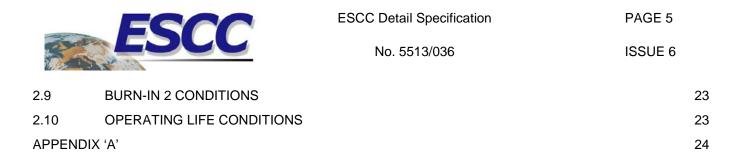
DCR No.	CHANGE DESCRIPTION
1111	Specification upissued to incorporate changes per DCR.



PAGE 4

TABLE OF CONTENTS

1	GENERAL	6
1.1	SCOPE	6
1.2	APPLICABLE DOCUMENTS	6
1.3	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	6
1.4	THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS	6
1.4.1	The ESCC Component Number	6
1.4.2	Component Type Variants	6
1.5	MAXIMUM RATINGS	9
1.6	HANDLING PRECAUTIONS	9
1.7	PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION	10
1.7.1	Ceramic Pill A (2 Leads) - Variants 01, 08, 15, 22, 29, 36	10
1.7.2	Ceramic Pill B - Variants 02, 09, 16, 23, 30, 37	11
1.7.3	Ceramic Pill C (Cathode Lead) - Variants 03, 10, 17, 24, 31, 38	12
1.7.4	Ceramic Pill D (Anode Lead) - Variants 04, 11, 18, 25, 32, 39	13
1.7.5	Ceramic Pill E (2 Leads) - Variants 05, 12, 19, 26, 33, 40	14
1.7.6	Ceramic Pill F (Anode Lead) - Variants 06, 13, 20, 27, 34, 41	15
1.7.7	Ceramic Pill G - Variants 07, 14, 21, 28, 35, 42	16
1.7.8	Ceramic Stripline - Variants 43 to 48	17
1.7.9	Die – Variants 49 to 54	18
1.8	FUNCTIONAL DIAGRAM	18
1.9	MATERIALS AND FINISHES	19
1.9.1	Materials and Finishes of Packaged Components	19
1.9.2	Materials and Finishes of Die Components	19
2	REQUIREMENTS	19
2.1	GENERAL	19
2.1.1	Deviations from the Generic Specification	19
2.1.1.1	Deviations from Qualification and Periodic Tests – Chart F4	19
2.2	MARKING	19
2.3	DIE SHEAR	19
2.4	TERMINAL STRENGTH	20
2.5	ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES	20
2.5.1	Room Temperature Electrical Measurements	20
2.5.2	High and Low Temperatures Electrical Measurements	21
2.6	PARAMETER DRIFT VALUES	22
2.7	INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS	22
2.8	BURN-IN 1 CONDITIONS	23





ISSUE 6

1 <u>GENERAL</u>

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5010
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u> The ESCC Component Number shall be constituted as follows:

Example: 551303601

- Detail Specification Reference: 5513036
- Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based On Type	Package Type / Description	$\begin{array}{c c} Total & Lead/Terminal \\ Capacitance & Material and \\ C_T (pF) & Finish (Note 1) \end{array}$		ial and	Weight Max (g)
			Max	Anode	Cathode	
01	DH50052	Ceramic Pill A (2 Leads)	0.21	E2	E2	0.02
02	DH50052	Ceramic Pill B	0.21	D7	D7	0.02
03	DH50052	Ceramic Pill C (Cathode Lead)	0.21	D7	E2	0.02
04	DH50052	Ceramic Pill D (Anode Lead)	0.21	E2	D7	0.02
05	DH50052	Ceramic Pill E (2 Leads)	0.21	E2	E2	0.02
06	DH50052	Ceramic Pill F (Anode Lead)	0.21	E2	D7	0.02
07	DH50052	Ceramic Pill G	0.28	D7	A7	0.15
08	DH50053	Ceramic Pill A (2 Leads)	0.25	E2	E2	0.02
09	DH50053	Ceramic Pill B	0.25	D7	D7	0.02
10	DH50053	Ceramic Pill C (Cathode Lead)	0.25	D7	E2	0.02

Packaged Components



Variant Based On Package Type Number Type		Package Type / Description	Total Capacitance C⊤ (pF)	Lead/T Mater Finish (Weight Max (g)	
			Max	Anode	Cathode	
11	DH50053	Ceramic Pill D (Anode Lead)	0.25	E2	D7	0.02
12	DH50053	Ceramic Pill E (2 Leads)	0.25	E2	E2	0.02
13	DH50053	Ceramic Pill F (Anode Lead)	0.25	E2	D7	0.02
14	DH50053	Ceramic Pill G	0.32	D7	A7	0.15
15	DH50054	Ceramic Pill A (2 Leads)	0.3	E2	E2	0.02
16	DH50054	Ceramic Pill B	0.3	D7	D7	0.02
17	DH50054	Ceramic Pill C (Cathode Lead)	0.3	D7	E2	0.02
18	DH50054	Ceramic Pill D (Anode Lead)	0.3	E2	D7	0.02
19	DH50054	Ceramic Pill E (2 Leads)	0.3	E2	E2	0.02
20	DH50054	Ceramic Pill F (Anode Lead)	0.3	E2	D7	0.02
21	DH50054	Ceramic Pill G	0.37	D7	A7	0.15
22	DH50055	Ceramic Pill A (2 Leads)	0.36	E2	E2	0.02
23	DH50055	Ceramic Pill B	0.36	D7	D7	0.02
24	DH50055	Ceramic Pill C (Cathode Lead)	0.36	D7	E2	0.02
25	DH50055	Ceramic Pill D (Anode Lead)	0.36	E2	D7	0.02
26	DH50055	Ceramic Pill E (2 Leads)	0.36	E2	E2	0.02
27	DH50055	Ceramic Pill F (Anode Lead)	0.36	E2	D7	0.02
28	DH50055	Ceramic Pill G	0.43	D7	A7	0.15
29	DH50056	Ceramic Pill A (2 Leads)	0.53	E2	E2	0.02
30	DH50056	Ceramic Pill B	0.53	D7	D7	0.02
31	DH50056	Ceramic Pill C (Cathode Lead)	0.53	D7	E2	0.02
32	DH50056	Ceramic Pill D (Anode Lead)	0.53	E2	D7	0.02
33	DH50056	Ceramic Pill E (2 Leads)	0.53	E2	E2	0.02
34	DH50056	Ceramic Pill F (Anode Lead)	0.53	E2	D7	0.02
35	DH50056	Ceramic Pill G	0.6	D7	A7	0.15
36	DH50057	Ceramic Pill A (2 Leads)	0.73	E2	E2	0.02
37	DH50057	Ceramic Pill B	0.73	D7	D7	0.02
38	DH50057	Ceramic Pill C (Cathode Lead)	0.73	D7	E2	0.02
39	DH50057	Ceramic Pill D (Anode Lead)	0.73	E2	D7	0.02
40	DH50057	Ceramic Pill E (2 Leads)	0.73	E2	E2	0.02
41	DH50057	Ceramic Pill F (Anode Lead)	0.73	E2	D7	0.02
42	DH50057	Ceramic Pill G	0.8	D7	A7	0.15
43	DH50052	Ceramic Stripline	0.22	D7	D7	0.02
44	DH50053	Ceramic Stripline	0.26	D7	D7	0.02
45	DH50054	Ceramic Stripline	0.31	D7	D7	0.02



PAGE 8

Variant Number	Based On Type	Package Type / Description	Capacitance Material and C⊤ (pF) Finish (Note		ial and	Weight Max (g)
			Max	Anode	Cathode	
46	DH50055	Ceramic Stripline	0.37	D7	D7	0.02
47	DH50056	Ceramic Stripline	0.54	D7	D7	0.02
48	DH50057	Ceramic Stripline	0.74	D7	D7	0.02

Die Components (Note 2)

Variant Number	Based On Type	Junction Capacitance C _J (pF) Max	Total Capacitance C⊤ (pF) Max (Note 3)
49	EH50052	0.08	0.28
50	EH50053	0.12	0.32
51	EH50054	0.17	0.37
52	EH50055	0.23	0.43
53	EH50056	0.4	0.6
54	EH50057	0.6	0.8

NOTES:

- 1. The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.
- 2. For Die Components, Variants 49 to 54, the default package selected for assembly of the Packaged Test Sublot shall be Ceramic Pill G. At the Manufacturer's option, any of the other packages specified herein with a Variant for the same die may be selected. The die applicable to each Variant is indicated by the based on type number.
- 3. In cases where the default package is not selected for the Packaged Test Sublot, the Total Capacitance limit of the selected package shall apply.



ISSUE 6

PAGE 9

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
DC Reverse Voltage	V _{Rmax}	-50	V	I _R = 10μΑ
DC Forward Current (Continuous) Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41: Variants 07, 14: Variants 21, 28, 35, 42: Variants 43 to 48:	I _{Fmax}	150 180 240 90	mA	Note 1
RF Power Dissipation Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41: Variants 07, 14: Variants 21, 28, 35, 42: Variants 43 to 48:	P _{tot}	0.5 0.62 0.83 0.3	V	Note 2
Operating Temperature Range	T _{op}	-55 to +150	°C	T _{case}
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Junction Temperature	Tj	+150	°C	
Thermal Resistance, Junction-to-Case Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41: Variants 07, 14, 49, 50: Variants 21, 28, 35, 42, 51 to 54: Variants 43 to 48:	R _{th(j-c)}	150 120 90 250	°C/W	Note 3
Soldering Temperature	T _{sol}	+230	°C	Note 4

NOTES:

- 1. At $T_{case} \le +75^{\circ}$ C. For $T_{case} > +75^{\circ}$ C, derate linearly to 0A at $T_{case} = +150^{\circ}$ C.
- 2. At $T_{case} \le +75^{\circ}$ C. For $T_{case} > +75^{\circ}$ C, derate linearly to 0W at $T_{case} = +150^{\circ}$ C.
- 3. Thermal Resistance ratings for Die Components, Variants 49 to 54, refer to the Packaged Test Sublot assembled in the default Ceramic Pill G package. In cases where the default package is not used, the Thermal Resistance rating associated with the package used and the same die shall apply
- 4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed. Only applicable to Variants 01 to 48 (Packaged Components).

1.6 HANDLING PRECAUTIONS

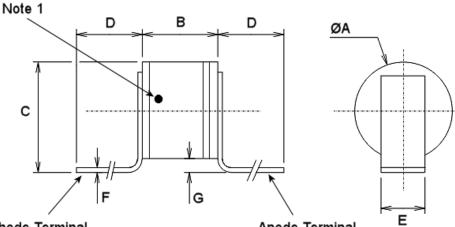
These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a Minimum Critical Path Failure Voltage of 500V.



1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 Ceramic Pill A (2 Leads) - Variants 01, 08, 15, 22, 29, 36



Cathode Terminal

Anode Terminal

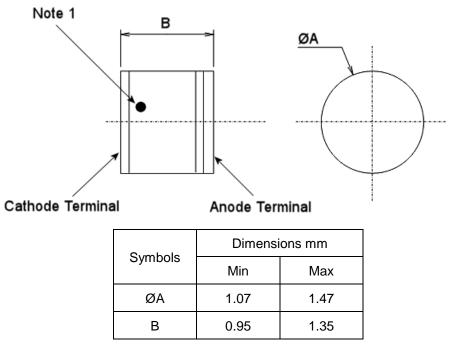
Symbolo	Dimensions mm		Remarks
Symbols	Min	Max	Remarks
ØA	1.07	1.47	
В	0.95	1.35	
С	1.3	1.9	Both terminals
D	2.5	-	
E	0.55	0.65	Both terminals
F	0.06	0.1	Both terminals
G	0.1	0.5	Both terminals

NOTES:



ISSUE 6

1.7.2 Ceramic Pill B - Variants 02, 09, 16, 23, 30, 37



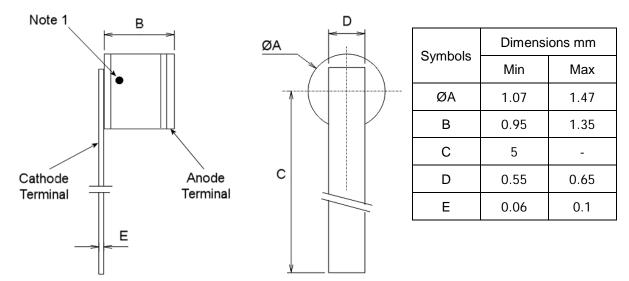
NOTES:



No. 5513/036

ISSUE 6

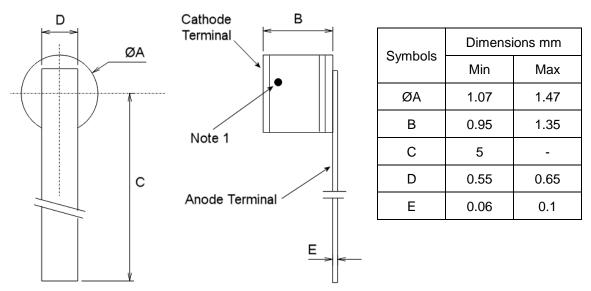
1.7.3 Ceramic Pill C (Cathode Lead) - Variants 03, 10, 17, 24, 31, 38



NOTES:



1.7.4 Ceramic Pill D (Anode Lead) - Variants 04, 11, 18, 25, 32, 39

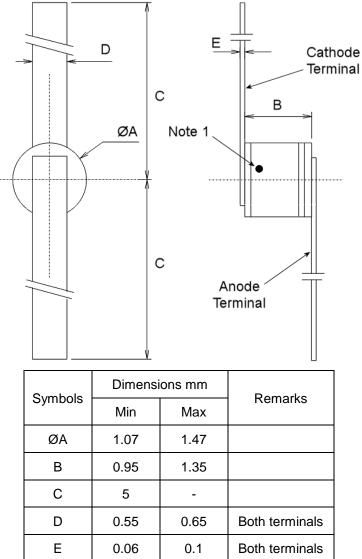


NOTES:



ISSUE 6

1.7.5 Ceramic Pill E (2 Leads) - Variants 05, 12, 19, 26, 33, 40

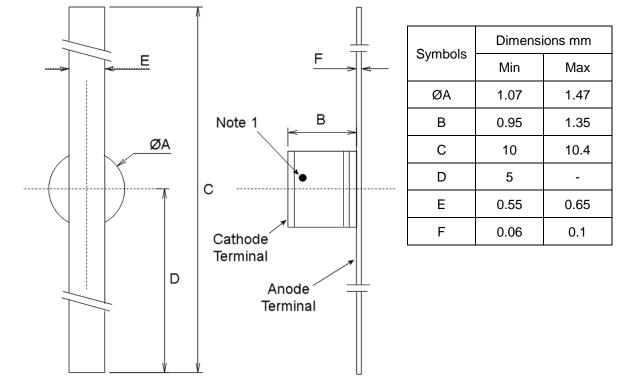


NOTES:



ISSUE 6

1.7.6 Ceramic Pill F (Anode Lead) - Variants 06, 13, 20, 27, 34, 41



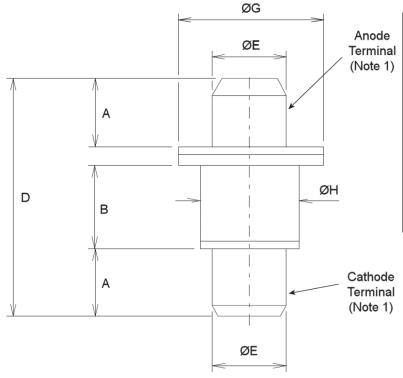
NOTES:



No. 5513/036

ISSUE 6

1.7.7 Ceramic Pill G - Variants 07, 14, 21, 28, 35, 42



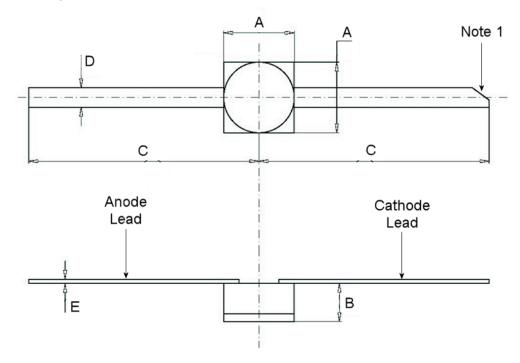
Symbols	Dimensions mm		
Symbols	Min	Max	
А	1.52	1.63	
В	1.75	1.85	
D	5.2	5.72	
ØE	1.52	1.63	
ØG	3	3.23	
ØН	1.95	2.11	

NOTES:

Terminal identification shall be by means of the physical configuration of the package.



1.7.8 Ceramic Stripline - Variants 43 to 48

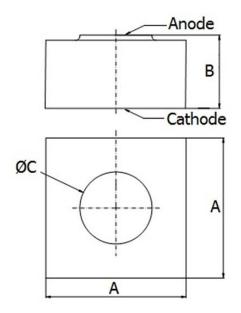


Symbole	Dimensi	Remarks	
Symbols	Min	Max	Remarks
А	1.68	1.88	
В	0.91	1.01	
С	6.15	6.55	
D	0.45	0.55	Both leads
E	0.08	0.12	Both leads

NOTES: 1. Terminal identification: The end of the cathode lead shall have a 45° chamfer.



1.7.9 Die – Variants 49 to 54



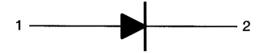
Symbols	Dimensions mm		Remarks
Symbols	Min	Max	Remarks
А	0.34	0.4	
В	0.16	0.26	
	0.02	0.06	Variant 49
	0.03	0.07	Variant 50
ØC	0.04	0.08	Variant 51
ØC	0.05	0.1	Variant 52
	0.06	0.12	Variant 53
	0.08	0.14	Variant 54

NOTES:

2.

- 1. Terminal identification shall be by means of the physical configuration.
 - Die construction, materials, finishes:
 - Die substrate: Silicon
 - Bond pad: The metallisation shall be TiPtAu with a layer of vacuum-deposited gold of thickness 0.7µm minimum.
 - Die backface: The metallisation shall be TiPtAu with a layer of gold of thickness 0.7µm minimum.
 - Glassivation: Silicon oxide of thickness 0.5µm typical.

1.8 FUNCTIONAL DIAGRAM



1. Anode

2. Cathode

NOTES:

1. For Variants 43 to 48, the lid is isolated from the terminals.



1.9 MATERIALS AND FINISHES

- 1.9.1 <u>Materials and Finishes of Packaged Components</u> For Variants 01 to 48, the materials and finishes shall be as follows:
 - (a) Case The case shall be hermetically sealed and have a ceramic body with a metal base and lid.
 - (b) Leads/Terminals As specified in Para. 1.4.2.
- 1.9.2 <u>Materials and Finishes of Die Components</u> For Variants 49 to 54, the materials and finishes shall be as specified in Para. 1.7.9.

2 <u>REQUIREMENTS</u>

2.1 <u>GENERAL</u>

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 <u>Deviations from the Generic Specification</u>

- 2.1.1.1 Deviations from Qualification and Periodic Tests Chart F4
 - (a) Mechanical Shock: Shall not be performed.
 - (b) Vibration: Shall not be performed.
 - (c) Constant Acceleration: Shall not be performed.

2.2 <u>MARKING</u>

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component or its primary package shall be:

- (a) Terminal identification, as specified in Para. 1.7.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

2.3 <u>DIE SHEAR</u>

In those cases where package clearances are such that a die shear test is not practicable, the die shall be pushed away with a suitable tool. The force required to remove the die need not be recorded. The die attachment area shall be inspected and the component shall be considered acceptable if more than 50% of the semiconductor material remains.



ISSUE 6

2.4 <u>TERMINAL STRENGTH</u>

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

- For Variants 01, 03 to 06, 08, 10 to 13, 15, 17 to 20, 22, 24 to 27, 29, 31 to 34, 36, 38 to 41, 43 to 48: Test Condition A, tension, with a force of 1.25N for duration 10s.
- For Variants 02, 07, 09, 14, 16, 21, 23, 28, 30, 35, 37, 42: shall not be performed.
- For Variants 49 to 54: not applicable.

2.5 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

2.5.1 <u>Room Temperature Electrical Measurements</u>

The measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

Characteristics	Symbols MIL-STD-750 Test Conditions		Lir	nits	Units	
		Test Method		Min	Max	
Reverse Current 1 (Note 1)	I _{R1}	4016	V _R = -50V	-	10	μA
Reverse Current 2 (Note 1)	I _{R2}	4016	V _R = -25V	-	100	nA
Forward Voltage (Note 1)	VF	4011	I⊧ = 10mA	-	1.1	V
Thermal Resistance, Junction-to-Case (Note 2)	Rth(j-c)	3101	Note 3	-	Note 4	°C/W
Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41, 43 to 48:						
,			P = 0.25W			
Variants 07, 14, 21, 28, 35, 42, 49 to 54:			P = 0.5W			
Total Capacitance (Note 2)	Ст	4001	$V_R = -6V, f = 1MHz$	-	Note 5	pF
Junction Capacitance (Note 6)	CJ	4001	$V_R = -6V$, f = 1MHz	-	Note 5	pF
Forward Series Resistance (Note 1)	R _{SF}	4056	I _F = 10mA f = 120MHz			Ω
Variants 01 to 07, 43, 49:				-	1.6	
Variants 08 to 14, 44, 50: Variants 15 to 21, 45, 51:				-	1.4 1.1	
Variants 15 to 21, 45, 51. Variants 22 to 28, 46, 52:				-	1.1	
Variants 29 to 35, 47, 53:				-	0.9	
Variants 36 to 42, 48, 54:				-	0.7	



Characteristics	Symbols		Test Conditions	Lin	nits	Units
		Test Method		Min	Max	
Minority Carrier Lifetime (Note 7)	τL	4031	I _F = 10mA I _R = 6mA			ns
Variants 01 to 07, 08 to 14, 43, 44, 49, 50: Variants 15 to 21, 45, 51: Variants 22 to 28, 46, 52: Variants 29 to 35, 47, 53: Variants 36 to 42, 48, 54:					60 70 80 100 120	

NOTES:

- 1. This characteristic applies to all Variants tested during Charts F2 and F3 of the Generic Specification.
- This characteristic applies to Variants 01 to 48 (Packaged Components) and Variants 49 to 54 (Packaged Test Sublot samples for Die Components), tested only during Chart F3 of the Generic Specification.
- 3. Pulsed measurement, pulse width = 10ms.
- 4. See Para. 1.5 for the applicable limits.
- 5. See Para. 1.4.2 for the applicable limits.
- 6. This characteristic only applies to Variants 49 to 54 (Die Components), tested only during Chart F2 of the Generic Specification.
- 7. Only performed during Chart F2 of the Generic Specification, on a sample of 27 dice per wafer. In the event of any failure, a 100% inspection shall be performed and all failures shall be clearly identified.

2.5.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed only at T_{amb} = +150 (+0 -3)°C.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Reverse Current 2 (Note 2)	I _{R2}	4016	V _R = -25V	-	1	μA

NOTES:

- 1. Measurements shall be performed on a sample basis as specified in the Generic Specification.
- 2. This characteristic applies to all Variants tested during Charts F2 and F3 of the Generic Specification.



No. 5513/036

ISSUE 6

2.6 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.5.1, Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift	Abso	Absolute	
		Value (1) Δ	Min	Max	
Reverse Current 2	I _{R2}	±10 or (2) ±100%	-	100	nA
Forward Voltage	VF	±5%	-	1.1	V
Total Capacitance (Note 3)	Ст	±5% (4) or ±10% (5)	-	Note 6	pF

NOTES:

- 1. $\Delta 1 = \Delta 2$.
- 2. Whichever is the greater referred to the initial value.
- 3. This characteristic applies to Variants 01 to 48 (Packaged Components) and Variants 49 to 54 (Packaged Test Sublot samples for Die Components).
- 4. Applicable drift value for $C_T > 0.5pF$ and rounded upwards to the nearest 0.01pF.
- 5. Applicable drift value for $C_T \le 0.5 pF$ and rounded upwards to the nearest 0.01 pF.
- 6. See Para. 1.4.2 for the applicable limits.

2.7 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.5.1, Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Reverse Current 1	I _{R1}	-	10	μA
Reverse Current 2	I _{R2}	-	100	nA
Forward Voltage	VF	-	1.1	V
Total Capacitance (Note 1)	Ст	-	Note 2	pF

NOTES:

- 1. This characteristic applies to Variants 01 to 48 (Packaged Components) and Variants 49 to 54 (Packaged Test Sublot samples for Die Components).
- 2. See Para. 1.4.2 for the applicable limits.



2.8 **BURN-IN 1 CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150 (+0 -3)	°C
Reverse Voltage (Note 1)	VR	-37.5	V

 $\label{eq:states} \begin{array}{ll} \underline{\text{NOTES:}} \\ 1. & \text{Upon completion of Burn-in 1, the test voltage shall be maintained until $T_{amb} < +35^{\circ}C$. \\ \end{array}$

2.9 **BURN-IN 2 CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Case Temperature	T _{case}	+125 (+0 -3)	°C
Forward Current	lF		mA
Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41:		50	
Variants 07, 14, 49, 50:		60	
Variants 21, 28, 35, 42, 51 to 54:		80	
Variants 43 to 48:		30	

2.10 **OPERATING LIFE CONDITIONS**

The conditions shall be as specified in Para. 2.9.



PAGE 24 ISSUE 6

APPENDIX 'A'

AGREED DEVIATIONS FOR COBHAM MICROWAVE (F)

Items Affected	Description of Deviations
Para. 2.1.1, Deviations from the Generic Specification:	SEM Inspection: From each wafer selected for SEM Inspection, the sample of three dice shall be selected after die separation.
Deviations from Special In- Process Controls – Chart F2	Bond Strength: The following pre-seal bond strength shall apply:0.03N minimum
Para. 2.1.1, Deviations from the Generic Specification: Deviations from Screening Tests for Packaged Components – Chart F3A	 Radiographic Inspection: May be performed without serialisation and at any point during Chart F3A. Any components found to fail Radiographic Inspection shall be removed from the lot. May be performed in the X and Z axes only.
Para. 2.1.1.1, Deviations from Qualification and Periodic Tests – Chart F4	 For the De-encapsulation Subgroup, the Internal Visual Inspection, Bond Strength and Die Shear tests may be replaced by measurements verifying the die solder integrity and wire integrity, as follows: Thermal Impedance test in accordance with MIL-STD-750, Test Method 3101.
	 For Variants 01 to 06, 08 to 13, 15 to 20, 22 to 27, 29 to 34, 36 to 41, 43 to 48: P_D = 0.25W. For Variants 07, 14, 21, 28, 35, 42, 49 to 54: P_D = 0.5W. The Thermal Impedance shall be measured and shall not exceed the applicable value of Thermal Resistance, Junction-to-Case specified in Para. 1.5 herein.
	 Forward Voltage test in accordance with MIL-STD-750, Test Method 4011. For Variants 01 to 42 and 49 to 54: I_F = 100mA. For Variants 43 to 48: I_F = 90mA. The Forward Voltage shall be measured and shall not exceed 1.2V.